

Remarks

Acceptance/formal entry therefor of this preliminarily submitted amendment in supplement to the Second Preliminary Amendment, filed on December 1, 2004, prior to the Examiner taking up the above-identified application for a formal review is respectfully requested.

The status of the claims is given above. Namely, there are currently pending claims 1-21, of which claims 1, 2, 16 and 17 are currently amended and claims 20 and 21 are newly presented. Independent claim 1 is being amended to correct a typographical error therein. Dependent claim 2 is also being amended to avoid any question of proper antecedent basis regarding the expression "said SRAM cell." Regarding dependent claim 16, a correction is being made of the claim dependency thereof. With regard to dependent claim 17, the expression "said first and second MISFETs" was revised to the expression said first and second field effect transistors, consistent with that set forth in the corresponding base claim 15. The additional set of new claims, i.e., claims 20-21, covers various other originally disclosed inventive aspects directed to a semiconductor integrated circuit device including SRAM cells. According to claims 20-21, the SRAM cell is constituted by a pair of n-channel drive MISFETs, a pair of p-channel load MISFETs and a pair of n-channel selection MISFETs, wherein both the drive and selection MISFETs contain a lightly doped drain (LDD) structure and the p-channel load MISFETs contain a single drain structure. An example of such a SRAM cell in which the drive and load MISFETs are configured as a pair of cross-connected inverter circuits and in which the input/output nodes thereof are coupled to the bit lines, via the selection (access) n-channel MISFETs, is shown in Figs. 11+ of the drawings, although not limited thereto. In Figs. 11+ the MISFETs with the thickened lines represent those whose source and drain regions have an offset structure.

It is submitted, the newly presented claims 20-21 as in claims 1+ *et seq.* are directed to subject matter containing SRAM cells which employ MISFETs. Examination and favorable action on the currently pending claims 1-21 is respectfully requested.

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Respectfully submitted,
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